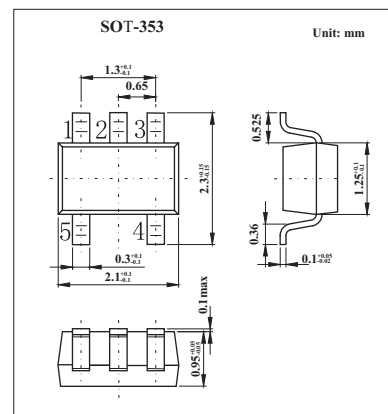
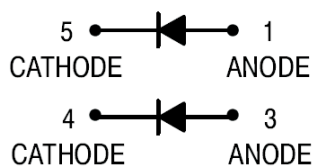


High Voltage Switching Diode BAS21DW5T1

■ Features

- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion
- High Conductance
- For General Purpose Switching Applications



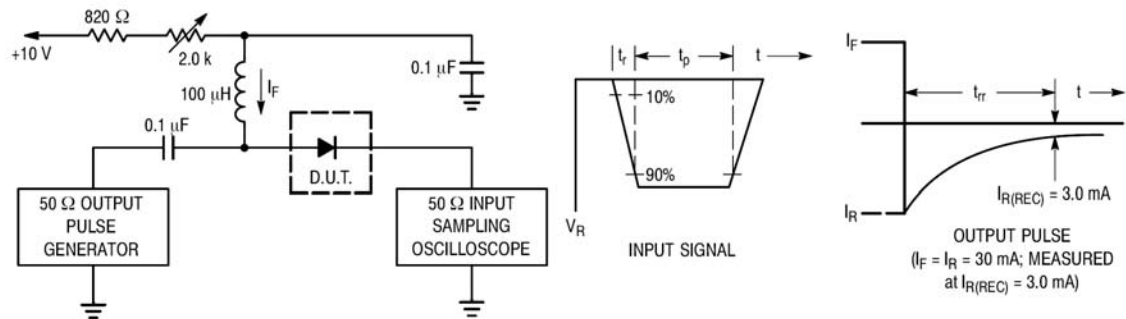
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_R	250	V
Peak Reverse Voltage	V_{RRM}	250	V
Forward Current	I_F	200	mA
Power Dissipation	P_D	385	mW
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R = 100 \mu\text{A}$	250			V
Forward Voltage	V_F	$I_F = 100\text{mA}$			1.0	V
		$I_F = 200\text{mA}$			1.25	
Reverse Leakage	I_R	$V_R = 200\text{V}$			0.1	μA
		$V_R = 200\text{V}, T_J = 150^\circ\text{C}$			100	
Junction Capacitance	C_j	$V_R = 0\text{V}, f = 1.0\text{MHz}$			5.0	pF
Reverse Recover Time	T_{rr}	$I_F = I_R = 30\text{mA}, I_{R(REC)} = 3.0\text{mA}, R_L = 100 \Omega$			50	nS

BAS21DW5T1



- Notes: 1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 30 mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
 3. $t_p \gg t_{rr}$

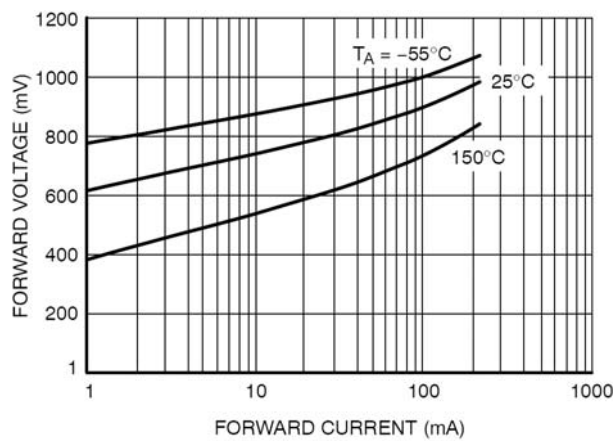


Figure 2. Forward Voltage

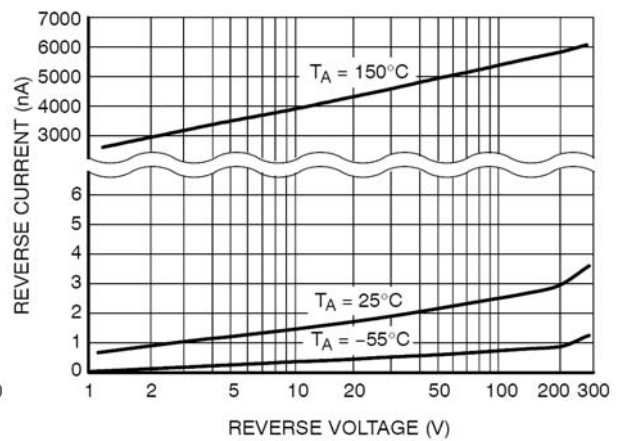


Figure 3. Reverse Leakage